Small Signal MOSFET

60 V, 380 mA, Single, N-Channel, SOT-23

Features

- ESD Protected
- Low R_{DS(on)}
- Surface Mount Package
- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	V
Gate-to-Source Voltage	V _{GS}	±20	V
	I _D	380 270	mA
	I _D	320 230	mA
Power Dissipation Steady State 1 sq in Pad Steady State Minimum Pad	P _D	420 300	mW
Pulsed Drain Current (t _p = 10 μs)	I _{DM}	5.0	Α
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Source Current (Body Diode)	I _S	300	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	TL	260	°C
Gate–Source ESD Rating (HBM, Method 3015)	ESD	2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Surface-mounted on FR4 board using 1 sq in pad size with 1 oz Cu.
- 2. Surface-mounted on FR4 board using 0.08 sq in pad size with 1 oz Cu.

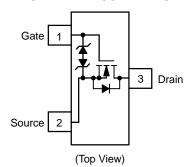


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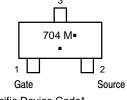
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
60 V	1.6 Ω @ 10 V	380 mA
	2.5 Ω @ 4.5 V	300 IIIA

SIMPLIFIED SCHEMATIC



MARKING DIAGRAM & PIN ASSIGNMENT

SOT-23 **CASE 318** STYLE 21



Drain

= Specific Device Code* 704 Μ = Date Code* = Pb-Free Package

(Note: Microdot may be in either location) *Specific Device Code, Date Code or overbar orientation and/or location may vary depending upon manufacturing location. This is a representation only and actual devices may not match this drawing exactly.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7002KT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
2V7002KT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)		300	°C/W
Junction-to-Ambient - t ≤ 5 s (Note 3)		92	
Junction-to-Ambient - Steady State (Note 4)		417	
Junction-to-Ambient - t ≤ 5 s (Note 4)		154	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•					•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				71		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V,	T _J = 25°C			1	μΑ
		V _{DS} = 60 V	T _J = 125°C			10	1
		V _{GS} = 0 V, V _{DS} = 50 V	T _J = 25°C			100	nA
Gate-to-Source Leakage Current	I_{GSS} $V_{DS} = 0 \text{ V, } V_{G}$		V _{GS} = ±20 V			±10	μΑ
		$V_{DS} = 0 V$	V _{GS} = ±10 V			450	nA
		V _{DS} = 0 V, V	/ _{GS} = ±5.0 V			150	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, I _D = 250 μA	1.0		2.3	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$ $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$			1.19	1.6	Ω
					1.33	2.5	
Forward Transconductance	9FS	$V_{DS} = 5 \text{ V}, I_{D} = 200 \text{ mA}$			530		mS
CHARGES AND CAPACITANCES							
Input Capacitance	C _{ISS}				24.5	45	pF
Output Capacitance	C _{OSS}		$V_{GS} = 0 \text{ V, } f = 1 \text{ MHz,}$ $V_{DS} = 20 \text{ V}$		4.2	8.0	
Reverse Transfer Capacitance	C _{RSS}	*DS	- 20 V		2.2	5.0	1
Total Gate Charge	$Q_{G(TOT)}$				0.7		nC
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 4.5 V	', V _{DS} = 10 V;		0.1		
Gate-to-Source Charge	Q_{GS}	I _D = 2	200 mA		0.3		
Gate-to-Drain Charge	Q_{GD}	-			0.1		
SWITCHING CHARACTERISTICS, V _{GS}	= V (Note 6)						
Turn-On Delay Time	t _{d(ON)}	$V_{GS} = 10 \text{ V}, V_{DD} = 25 \text{ V},$ $I_{D} = 500 \text{ mA}, R_{G} = 25 \Omega$			12.2		ns
Rise Time	t _r				9.0		
Turn-Off Delay Time	t _{d(OFF)}				55.8		
Fall Time	t _f				29		
DRAIN-SOURCE DIODE CHARACTER	ISTICS						
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V,	T _J = 25°C		0.8	1.2	V
		$I_S = 200 \text{ mA}$ $T_J = 85^{\circ}\text{C}$			0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulse Test: pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$

Surface–mounted on FR4 board using 1 sq in pad size with 1 oz Cu.
 Surface–mounted on FR4 board using 0.08 sq in pad size with 1 oz Cu.

^{6.} Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

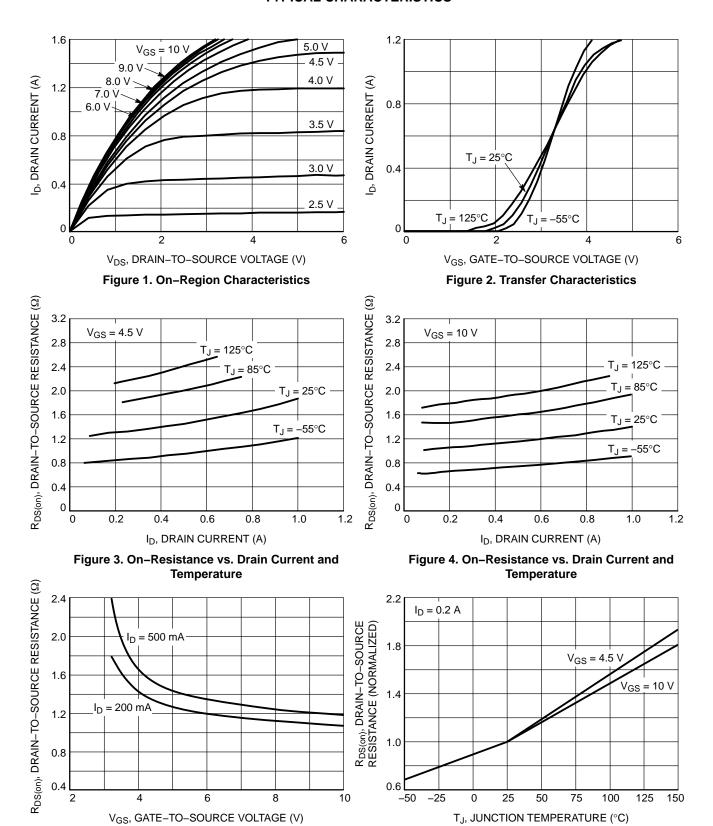


Figure 6. On-Resistance Variation with

Temperature

Figure 5. On-Resistance vs. Gate-to-Source

Voltage

TYPICAL CHARACTERISTICS

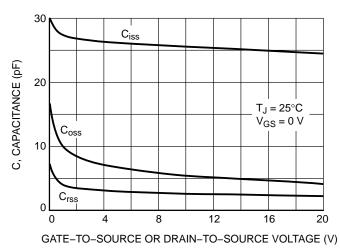


Figure 7. Capacitance Variation

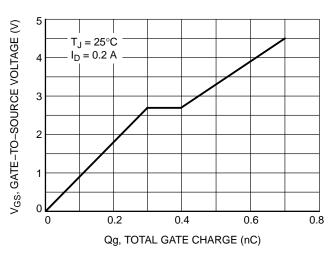


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

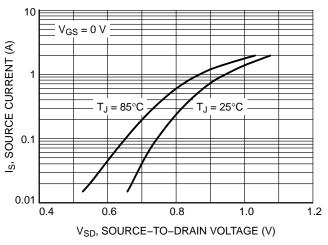


Figure 9. Diode Forward Voltage vs. Current

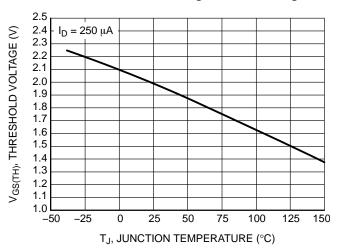


Figure 10. Threshold Voltage with Temperature

TYPICAL CHARACTERISTICS

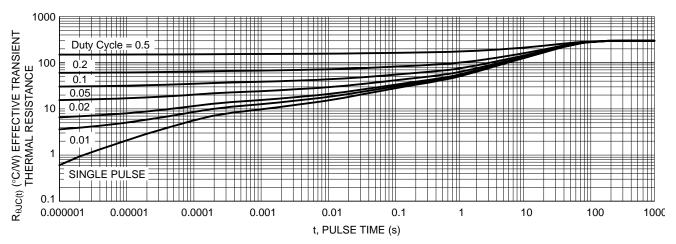


Figure 11. Thermal Response - 1 sq in pad

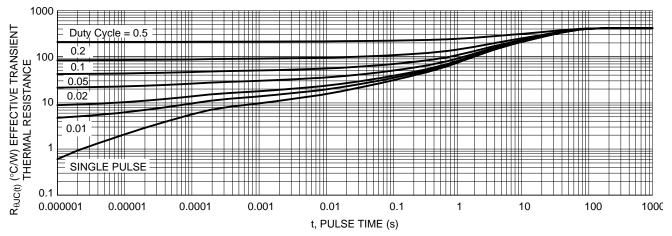
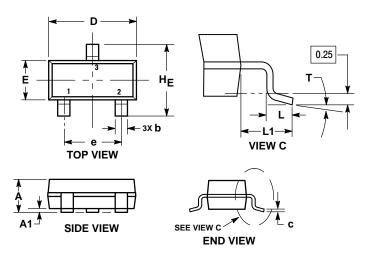


Figure 12. Thermal Response - minimum pad

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



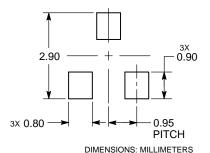
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
T	0°		10°	0°		10°	

STYLE 21:

- PIN 1. GATE
 - SOURCE 2.
 - DRAIN

RECOMMENDED SOLDERING FOOTPRINT



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